What is claimed is:

1. A liquid crystal display device, comprising:

a gate electrode on a substrate;

a gate insulating film on the substrate and over the gate electrode;

a semiconductor layer on the gate insulating film and over the gate electrode;

a source electrode and a drain electrode on the semiconductor layer and adjacent the gate electrode, wherein the source electrode and the drain electrode each include at least one protrusion that extends toward the other electrode;

a protective layer on the gate insulating film and over the source and drain electrodes; and

a pixel electrode on the protective layer.

2. The liquid crystal display device as claimed in claim 1, wherein the semiconductor layer includes a "ㄷ"-shaped channel.

3. The liquid crystal display device as claimed in claim 1, wherein the semiconductor layer includes:

an active layer on the gate insulating film; and

an ohmic contact layer on the active layer.

4. The liquid crystal display device as claimed in claim 3, wherein the ohmic contact layer includes an "ㄷ"-shaped opening that corresponds to the shape of the channel.

5. The liquid crystal display device as claimed in claim 3, wherein the active layer is undoped silicon.

6. The liquid crystal display device as claimed in claim 3, wherein the ohmic contact layer is doped silicon.

7. The liquid crystal display device as claimed in claim 2, wherein the channel has a width greater than 50 μm.

8. The liquid crystal display device as claimed in claim 2, wherein the channel extends over the gate electrode.

9. The liquid crystal display device as claimed in claim 1, wherein the pixel electrode contacts the drain electrode through an opening in the protective layer.

10. The liquid crystal display device as claimed in claim 1, further including a data line in electrical communication with the source electrode.

11. A method of fabricating a liquid crystal display device, comprising the steps of:

forming a gate electrode on a substrate;

forming a gate insulating film on the substrate and over the gate electrode;

forming a semiconductor layer on the gate insulating film and over the gate electrode;

forming source and drain electrodes on the semiconductor layer, wherein the source and drain electrodes each include at least one protrusion that extends toward the other electrode;

forming a protective layer over the source and drain electrodes and over a portion of the gate insulating film; and

forming a pixel electrode on the protective layer.

12. The method as claimed in claim 11, wherein the semiconductor layer forms a "ב"-shaped channel.

13. The method as claimed in claim 11, wherein forming a semiconductor layer includes:

forming an active layer on the gate insulating film; and

forming an ohmic contact layer formed on the active layer.

14. The method as claimed in claim 12, wherein forming an ohmic contact layer produces a "ב"-shaped opening that corresponds to the shape of the channel.

15. The method as claimed in claim 13, wherein the active layer is formed from undoped silicon.

16. The method as claimed in claim 13, wherein the ohmic contact layer is formed from doped silicon.

17. The method as claimed in claim 12, wherein the channel is formed with a length greater than 50 μm.

18. The method as claimed in claim 12, wherein the channel is formed only over the gate electrode.

19. The method as claimed in claim 11, wherein forming a protective layer includes forming an opening that exposes the drain electrode.

20. The method as claimed in claim 19, wherein forming a pixel electrode include forming the pixel electrode in electrical communication with the drain electrode.